

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	(chip or semiconductor) and (microwave\$3 with chamber) and (reflect\$3 with wall) and (absorb\$3 with (material or device\$1))	EPO; JPO; DERWE NT	2003/10/09 10:29
2	BRS	L2	25	(chip or semiconductor) and (microwave\$3 with chamber) and (reflect\$3 with wall) and (absorb\$3 with (material or device\$1))	USPAT; US-PGP UB; JPO; DERWE NT	2003/10/09 13:59
3	IS&R	L3	603	(219/690,502,121.43).CCLS.	USPAT	2003/10/09 13:55
4	IS&R	L4	805	(438/16,463,482).CCLS.	USPAT	2003/10/09 13:55
5	IS&R	L5	1167	(118/723AN,723MW,723MA,723ME,5 0.1).CCLS.	USPAT	2003/10/09 13:56
6	IS&R	L6	130	(156/345.42).CCLS.	USPAT	2003/10/09 13:57
7	BRS	L7	2603	3 or 4 or 5 or 6	USPAT	2003/10/09 13:57
8	BRS	L8	11	7 and (chip or semiconductor) and (microwave\$3 with chamber) and (reflect\$3 with wall) and (absorb\$3 with (material or device\$1))	USPAT; US-PGP UB; JPO; DERWE NT	2003/10/09 13:58
9	BRS	L9	0	8 not 2	USPAT; US-PGP UB; JPO; DERWE NT	2003/10/09 13:58
10	BRS	L10	25	(chip or semiconductor) and (microwave\$3 with chamber) and (reflect\$3 with wall) and (absorb\$3 with (material or device\$1))	USPAT; US-PGP UB; JPO; DERWE NT	2003/10/09 13:59